## Amendments to the claims:

(currently amended) An electric motor, in particular a starter device for internal combustion engines in which an electric resistor (57) with a negative temperature coefficient is connected at the beginning of the main current path (49) of an electromagnetically excitable rotor (53) of the electric motor (16), wherein the electric resistor (57) contains at least one monocrystalline semiconductor, wherein the monocrystalline semiconductor (80, 93) is comprised of high-doped silicon and at least one region (92) with low doping that is monocrystalline and is produced by means of epitaxy.

## (canceled)

- (currently amended) The electric motor as recited in claim 1/2, wherein a doping profile is produced in which a the high doping in a the region (90, 93) is approximately 1e20cm-3 and the at least one region (92) with the low doping has a doping between 1e14cm-3 and 1e15cm-3.
- 4. (currently amended) The electric motor as recited in claim 1/2, wherein a doping profile is produced so that within a predeterminable temperature range, in-particular-from 459—250°C; when there is a slight temperature change, the electric resistance of a the component changes by large amounts—in-particular by a factor of up to 100.

- (original) The electric motor as recited in claim 1, wherein the monocrystalline semiconductor (90, 93) is comprised of high-doped silicon and at least one region (95) with polycrystalline silicon.
- 6. (currently amended) The electric motor as recited in claim 5, wherein the parameters of the region with polycrystalline silicon are selected so that within a predeterminable temperature range, when there is a slight temperature change, the electric resistance of <u>a</u> the component changes by large amounts—in-particular by a factor of up to 100.
- (currently amended) The electric motor as recited in claim 6, wherein the predeterminable temperature range with a the resistance jump lies at approximately 200°C.
- (currently amended) The electric motor as recited in claim 1, wherein the monocrystalline semiconductor is comprised of a material with a high intrinsic charge carrier density and a predeterminable, in particular low[[,]] energy gap.
- (original) The electric motor as recited in claim 8,
  wherein the monocrystalline semiconductor is a germanium semiconductor.

- (currently amended) The electric motor as recited in claim 8, wherein the monocrystalline semiconductor is a composite semiconductor[[,]] in particular the form of a III-V semiconductor-preferably an InSb-or-InAs semiconductor.
- (currently amended) The electric motor as recited in claim 1,
  wherein the resistor (57) has a metallization (91, 94) on two both sides.
- (previously presented) The electric motor as redited in claim 1, wherein the resistor (57) is fastened in an integrally joined fashion between two conductors (80, 83, 86).
- (currently amended) The electric motor as recited in claim 12 4, wherein an the assembly comprised of the resistor (57) and the two conductors (80, 83, 88) is enclosed by a protective casing (85).
- (currently amended) The electric motor as recited in claim 13 4,
  wherein the casing (85) is a cover (59)
- (previously presented) A temperature-dependent resistor as recited in claim 1, wherein it is used to produce a predeterminable temperature dependency.

- (new) The electric motor as recited in claim 4, the predeterminable temperature range is 150 – 250°C.
- (new) The electric motor as recited in claim 10, wherein the monocrystalline semiconductor is an InSb or InAs semiconductor.